

Vladimir Litvinov

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Investigation of the properties of zinc oxide based heterostructures. Physics of Complex Systems, 2021, 2, 172-179.	0.2	0
2	External Quantum Efficiency of Bifacial HIT Solar Cells. Semiconductors, 2020, 54, 1254-1259.	0.5	3
3	Structural Dependent Eu ³⁺ Luminescence, Photoelectric and Hysteresis Effects in Porous Strontium Titanate. Materials, 2020, 13, 5767.	2.9	8
4	Deep-Level Defects in a Photovoltaic Converter with an Antireflection Porous Silicon Film Formed by Chemical Stain Etching. Technical Physics Letters, 2019, 45, 145-148.	0.7	1
5	Mechanisms of Current Flow in the Diode Structure with an n + p-Junction Formed by Thermal Diffusion of Phosphorus From Porous Silicon Film. Russian Physics Journal, 2018, 60, 1565-1571.	0.4	2
6	Application of Adaptive Algorithms for Measuring Temperature Current-Voltage Characteristics of Electronic Elements. , 2018, , .		0
7	Study of Nanoporous Carbon Fabrics for Rechargeable Energy Storage Capacitors. MRS Advances, 2018, 3, 3227-3232.	0.9	0
8	An Automated Measuring System for Current Deep-Level Transient Spectroscopy. Instruments and Experimental Techniques, 2018, 61, 277-282.	0.5	4
9	Excess noise and deep level defects diagnostics in semiconductor barrier structures. , 2018, , .		0
10	Investigation of Au/ZnO/Si MIS structures by capacitance-voltage characteristics method. , 2018, , .		0
11	Study of Current Flow Mechanisms in a CdS/por-Si/p-Si Heterostructure. Semiconductors, 2018, 52, 891-896.	0.5	0
12	Study of Deep Levels in a HIT Solar Cell. Semiconductors, 2018, 52, 926-930.	0.5	3
13	Defects with deep levels in a semiconductor structure of a photoelectric converter of solar energy with an antireflection film of porous silicon. Technical Physics Letters, 2017, 43, 955-957.	0.7	3
14	Investigation of Deep-Level Defects Lateral Distribution in Active Layers of Multicrystalline Silicon Solar Cells. MRS Advances, 2017, 2, 3141-3146.	0.9	1
15	Study of Nanoporous Carbon Fabrics for Rechargeable Energy Storage Capacitors. MRS Advances, 2017, 2, 3255-3261.	0.9	1
16	An investigation of current-flow mechanisms in thin rubrene wafers prepared by the vapor transport method. Technical Physics Letters, 2016, 42, 1107-1109.	0.7	0
17	Investigation of the Influence of Deep-Level Defects on the Conversion Efficiency of Sibased Solar Cells. MRS Advances, 2016, 1, 911-916.	0.9	5
18	Measuring complex for analysis of recombination deep traps in semiconductor solar cells. , 2015, , .		2

#	ARTICLE	IF	CITATIONS
19	Low-resistance and high-resistance states in strontium titanate films formed by the sol-gel method. <i>Physics of the Solid State</i> , 2015, 57, 2030-2033.	0.6	3
20	The measuring systems of semiconductor structures and its software. , 2015, , .		8
21	The Measurement of Electric Field Distribution in the Barrier Structures Based on Disordered Semiconductors. <i>Journal of Nanoelectronics and Optoelectronics</i> , 2015, 9, 773-777.	0.5	5
22	Complex Method of Diagnostics of Diode-Like Quantum Well Heterostructures with Use of Low Frequency Noise Spectroscopy. <i>Journal of Nanoelectronics and Optoelectronics</i> , 2015, 9, 756-761.	0.5	6
23	Apparatus for determining parameters of semiconductor structures by magnetic quantum effects and admittance spectroscopy. <i>Instruments and Experimental Techniques</i> , 2014, 57, 479-487.	0.5	1
24	Analysis of the electrostatic interaction of charges in multiple InGaAs/GaAs quantum wells by admittance-spectroscopy methods. <i>Semiconductors</i> , 2014, 48, 917-923.	0.5	6
25	A measuring System for the Spectroscopy of the Low-Frequency Noise of Semiconductor Diode Structures. <i>Measurement Techniques</i> , 2013, 56, 1066-1071.	0.6	2
26	Local study of the energy spectrum of electrons in CdSe/ZnSe QD structure by current DLTS cooperated with AFM. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 1772-1775.	0.8	0
27	Local measurement of conduction band offset for ZnCdS/ZnSSe nanostructure by Laplace current DLTS cooperated with AFM technique. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1536-1538.	0.8	1
28	Analysis of the parameters of deep centers in the Al/i-GaAs detectors of charged particles and X-ray radiation. <i>Journal of Communications Technology and Electronics</i> , 2007, 52, 1165-1170.	0.5	1
29	Cathodoluminescence and electrophysical characterization of Al _x Ga _{1-x} N epilayers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 2121-2124.	0.8	0
30	Electrophysical and cathodoluminescent properties of low-dimensional CdSSe/CdS structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1156-1159.	0.8	0
31	E-beam irradiation effect on CdSe/ZnSe QD formation by MBE: deep level transient spectroscopy and cathodoluminescence studies. <i>Journal of Physics Condensed Matter</i> , 2004, 16, S133-S140.	1.8	1
32	Deep-level transient spectroscopy and cathodoluminescence of Cd _x Zn _{1-x} Te/ZnTe QW structures grown on GaAs(100) by MBE. <i>Journal of Crystal Growth</i> , 2000, 214-215, 983-987.	1.5	3
33	Electrical Properties of ZnSe Epilayers on GaAs(001). <i>Inorganic Materials</i> , 2000, 36, 1203-1207.	0.8	0
34	Band alignment in ZnCdTe/ZnTe and ZnCdSe/ZnSe SQW structures grown on GaAs(100) by MBE. <i>Nanotechnology</i> , 2000, 11, 241-245.	2.6	9